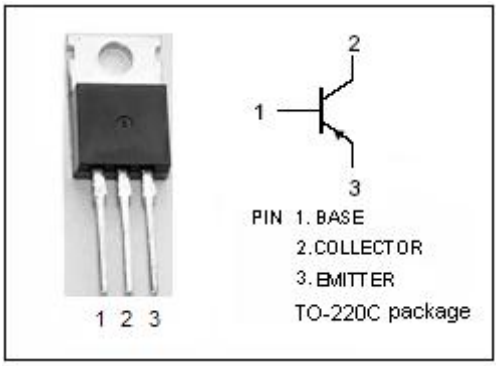
SPTECH Silicon PNP Power Transistor

DESCRIPTION

- DC Current Gain -h_{FE} =30(Min)@ I_C= -0.3A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = -45V(Min)- BD243; -60V(Min)- BD243A
  -80V(Min)- BD243B; -100V(Min)- BD243C
- Complement to Type BD243/A/B/C

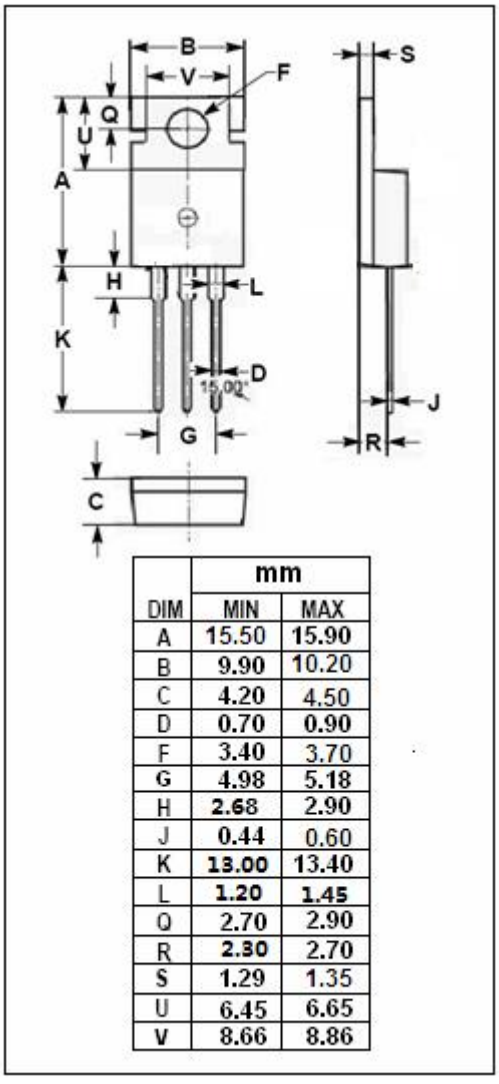


APPLICATIONS

- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER		VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BD244	-45	V
		BD244A	-60	
		BD244B	-80	
		BD244C	-100	
V_{CEO}	Collector-Emitter Voltage	BD244	-45	V
		BD244A	-60	
		BD244B	-80	
		BD244C	-100	
V_{EBO}	Emitter-Base Voltage		-5	V
I_C	Collector Current-Continuous		-6.0	A
I_{CM}	Collector Current-Peak		-10	A
I_B	Base Current		-2.0	A
P_C	Collector Power Dissipation @ T_C=25℃		65	W
T_J	Junction Temperature		150	℃
T_{stg}	Storage Temperature Range		-65~150	℃



DIM	mm MIN	MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	1.92	℃/W

SPTECH Silicon PNP Power Transistor

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	BD244	I_C= -30mA ;I_B=0	-45		V
		BD244A		-60		
		BD244B		-80		
		BD244C		-100		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage		I_C= -6A; I_B= -1A		-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage		I_C= -6A ; V_{CE}= -4V		-2.0	V
I_{CES}	Collector Cutoff Current	BD244	V_{CE}= -45V; V_{BE}= 0		-0.4	mA
		BD244A	V_{CE}= -60V; V_{BE}= 0			
		BD244B	V_{CE}= -80V; V_{BE}= 0			
		BD244C	V_{CE}= -100V; V_{BE}= 0			
I_{CEO}	Collector Cutoff Current	BD244/A	V_{CE}= -30V;I_B= 0		-0.7	mA
		BD244B/C	V_{CE}= -60V;I_B= 0			
I_{EBO}	Emitter Cutoff Current		V_{EB}= -5V; I_C= 0		-1.0	mA
h_{FE-1}	DC Current Gain		I_C= -0.3A ; V_{CE}= -4V	30		
h_{FE-2}	DC Current Gain		I_C= -3A ; V_{CE}= -4V	15		
f_T	Current-Gain—Bandwidth Product		I_C= -0.5A ; V_{CE}= -10V, f_{test}= 1.0MHz	3.0		MHz